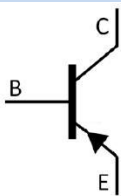


Silicon PNP transistor in a TO-126F Plastic Package.

Complement to BD135.

Medium power linear and switching applications.

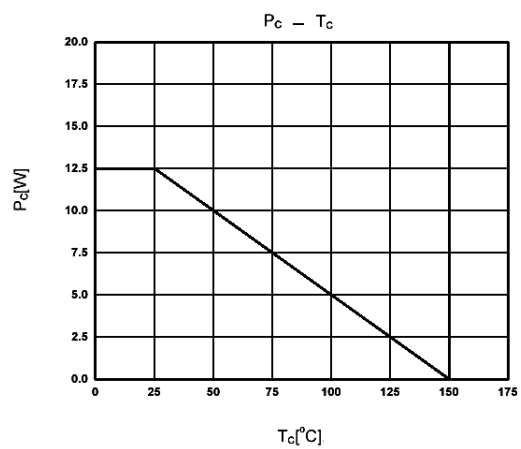
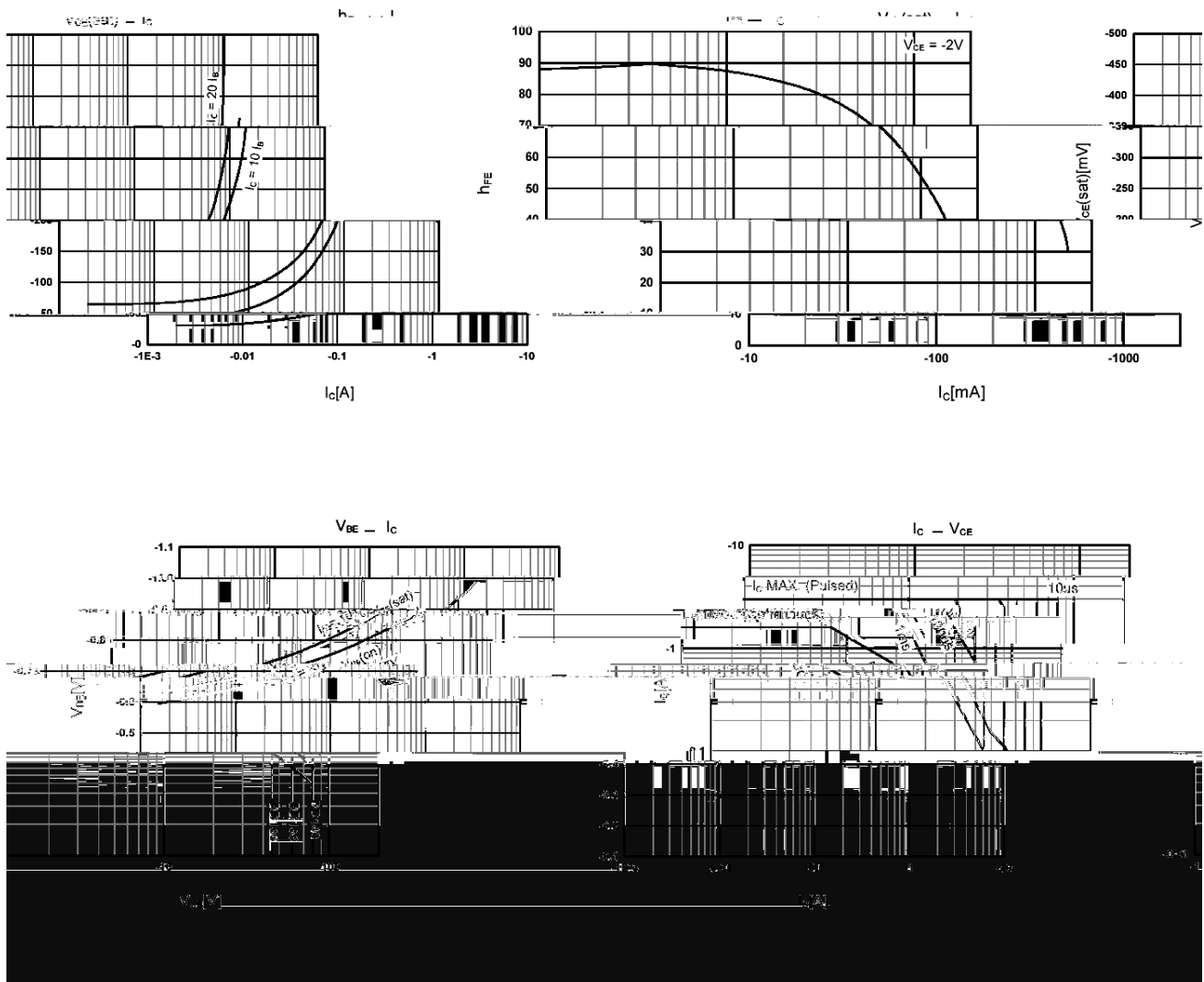


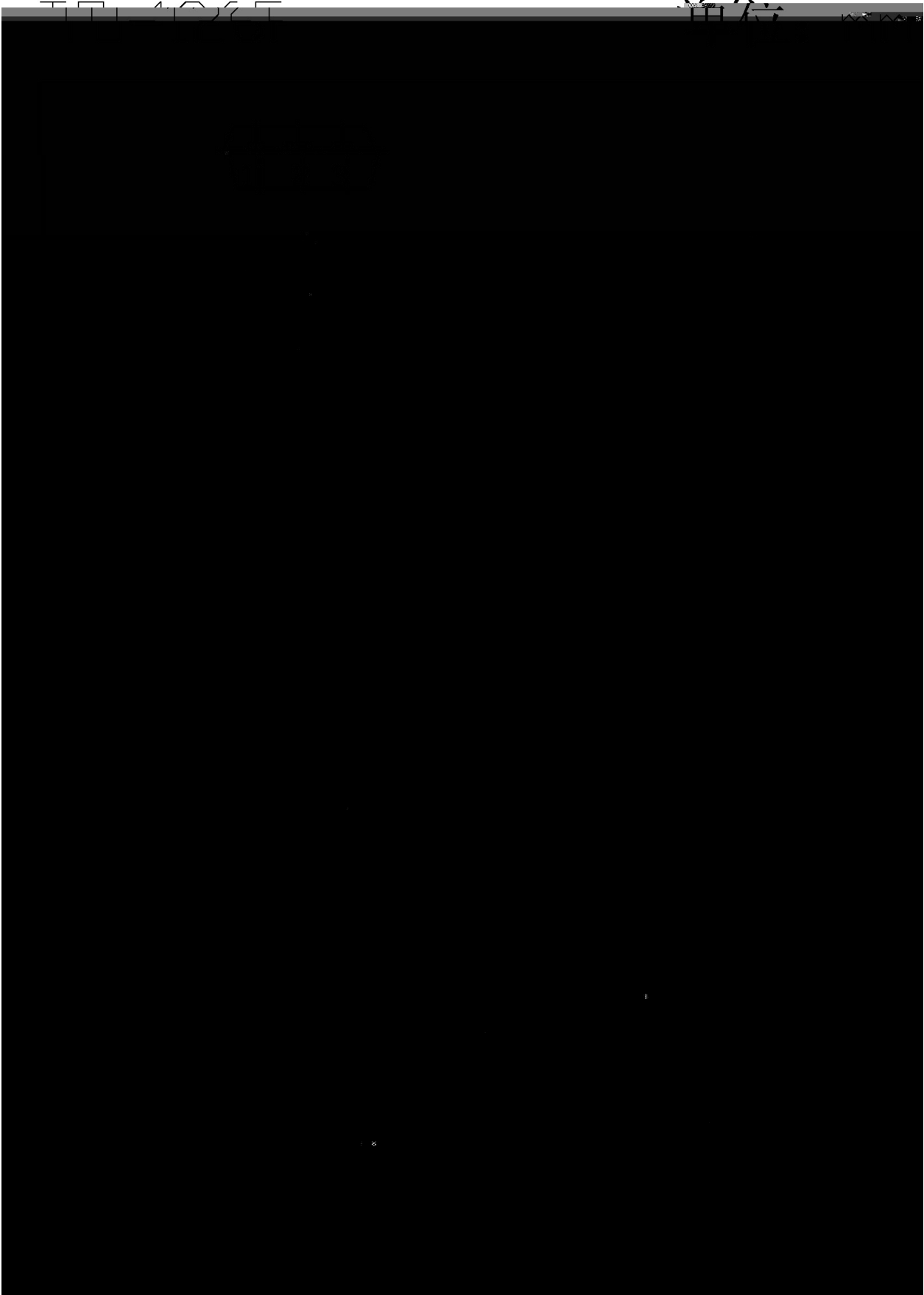
PIN1 Emitter PIN 2 Collector PIN 3 Base

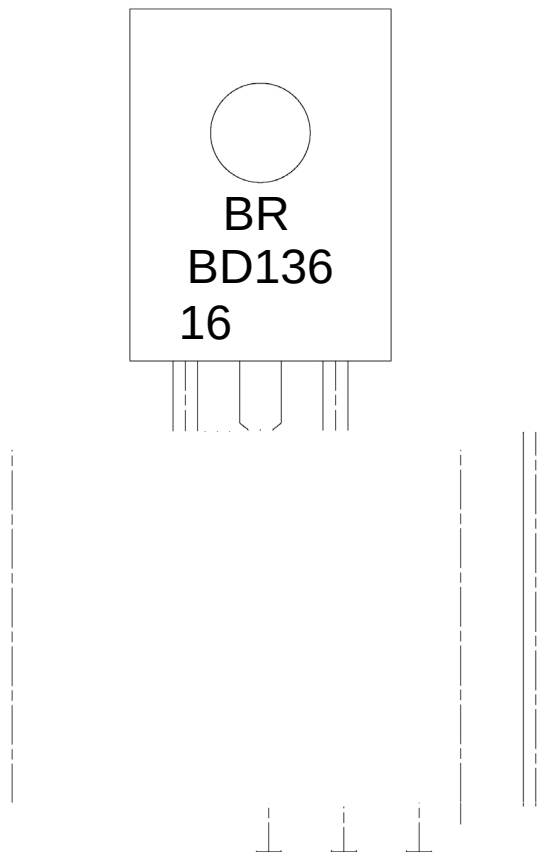
h_{FE} Classifications Symbol	6	10	16
h_{FE} Range	40 100	63 160	100 250

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-45	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-1.5	A
Collector Current – Continuous	I_{CP}	-3.0	A
Base Current – Continuous	I_B	-0.5	A
Collector Power Dissipation	P_C	1.25	W
Collector Power Dissipation	$P_C(T_c=25^{\circ}\text{C})$	12.5	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-30\text{mA}$ $I_B=0$	-45			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30\text{V}$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0\text{V}$ $I_C=0$			-10	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2.0\text{V}$ $I_C=-150\text{mA}$	40		250	
	$h_{FE(2)}$	$V_{CE}=-2.0\text{V}$ $I_C=-500\text{mA}$	25			
	$h_{FE(3)}$	$V_{CE}=-2.0\text{V}$ $I_C=-5.0\text{mA}$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$ $I_B=-50\text{mA}$			-0.5	V
Base to Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=-2.0\text{V}$ $I_C=-500\text{mA}$			-1.0	V







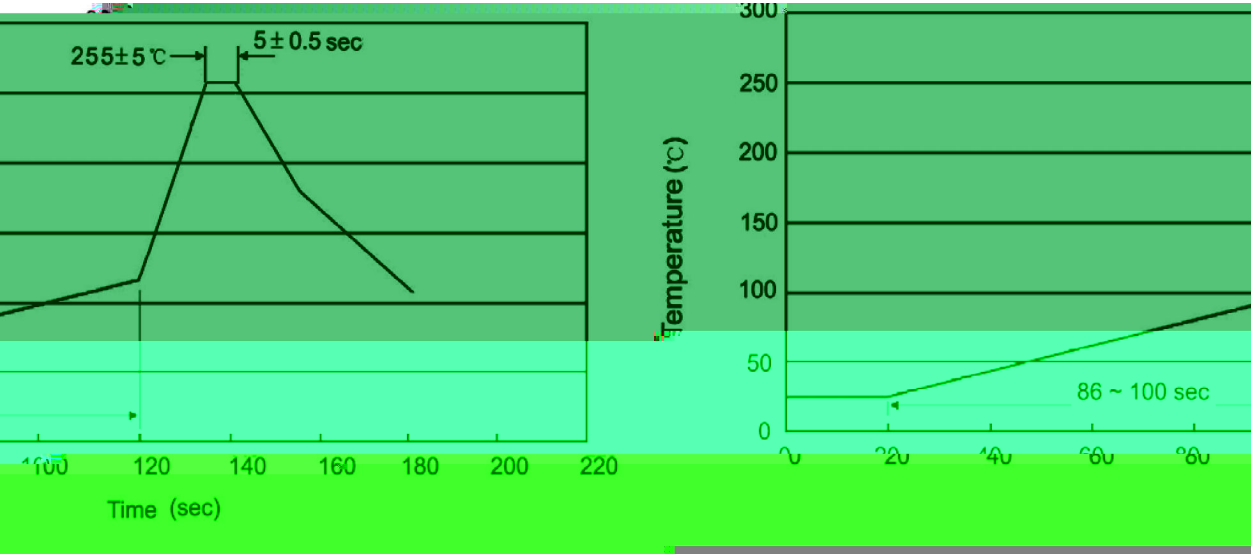
Note:

BR: Company Code

BD136: Product Type.

16: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



- Note:

1. Preheating: 25~150 , Time: 60~90sec.

2. Peak Temp.: 255±5 , Duration: 5±0.5sec.

3. Cooling Speed: 2~10 /sec.
- 1 25 150 60 90sec;

2 255±5 5±0.5sec;

3 2~10 /sec.

270±5

10±1 sec.

Temp.: 270±5°C

Time: 10±1 sec

/ BULK

Package Type	Units	Dimension	(unit mm ³)
--------------	-------	-----------	-------------------------